

ABSTRACT OF THE DISCLOSURE

A method of fabricating complementary high-voltage field-effect transistors in a substrate of a first conductivity type includes forming first and second well regions of a second conductivity type in the substrate. A first drain region of the second conductivity type is formed in the first well region, and a first source region is formed in the substrate adjacent the first well region. Second and third drain regions of the first conductivity type are formed in the second well region separated from one another. A second source region of the first conductivity type is formed in the second well region separated from the second drain region. First and second buried layers are formed within the first and second well regions, respectively, with the second buried layer connected to the second and third drain regions.